PD - 95283

International
IOR Rectifier

IRF7488PbF

HEXFET® Power MOSFET

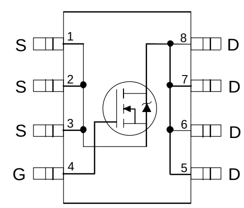
Applications

- High frequency DC-DC converters
- Lead-Free

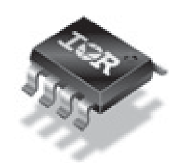
V_{DSS}	$R_{DS(on)}$ max	Q_g
80V	29mΩ@V_{GS}=10V	38nC

Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C_{OSS} to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



Top View



SO-8

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	6.3	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	5.0	
I_{DM}	Pulsed Drain Current ①	50	
P_D @T_A = 25°C	Maximum Power Dissipation	2.5	W
P_D @T_A = 70°C	Maximum Power Dissipation	1.6	
	Linear Derating Factor	20	mW/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	–––	20	
$R_{\theta JA}$	Junction-to-Ambient ④	–––	50	°C/W

Notes ① through ④ are on page 9

09/21/04

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	80	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.089	–––	V/°C	Reference to 25°C, I_D = 1mA ③
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	24	29	mΩ	V_{GS} = 10V, I_D = 3.8A ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–––	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	20	µA	V_{DS} = 80V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 64V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	200	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-200		V_{GS} = -20V

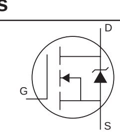
Dynamic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	9.3	–––	–––	S	V_{DS} = 15V, I_D = 3.8A
Q_g	Total Gate Charge	–––	38	57	nC	I_D = 3.8A
Q_{gs}	Gate-to-Source Charge	–––	9.1			V_{DS} = 40V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	12			V_{GS} = 10V,
$t_{d(on)}$	Turn-On Delay Time	–––	13	–––	ns	V_{DD} = 40V
t_r	Rise Time	–––	12	–––		I_D = 3.8A
$t_{d(off)}$	Turn-Off Delay Time	–––	44	–––		R_G = 9.1Ω
t_f	Fall Time	–––	16	–––		V_{GS} = 10V ③
C_{iss}	Input Capacitance	–––	1680	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	270	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	32	–––		f = 1.0MHz
C_{oss}	Output Capacitance	–––	1760	–––		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	–––	170	–––		V_{GS} = 0V, V_{DS} = 64V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	–––	340	–––		V_{GS} = 0V, V_{DS} = 0V to 64V ⑤

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	–––	96	mJ
I_{AR}	Avalanche Current①	–––	3.8	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	50		
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 3.8A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	–––	65	98	ns	T_J = 25°C, I_F = 3.8A
Q_{rr}	Reverse RecoveryCharge	–––	190	290	nC	di/dt = 100A/µs ③

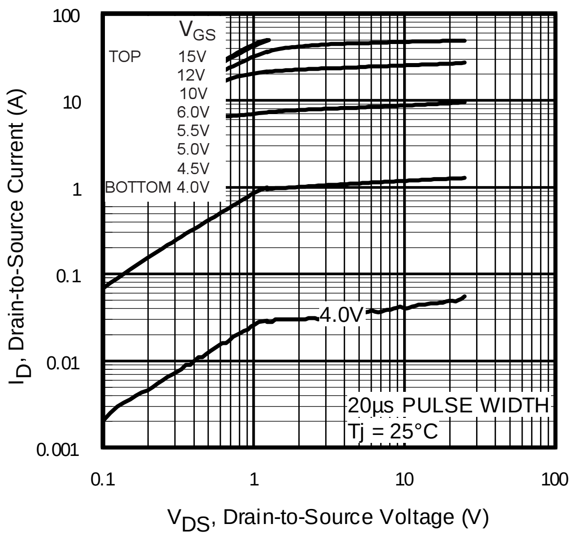


Fig 1. Typical Output Characteristics

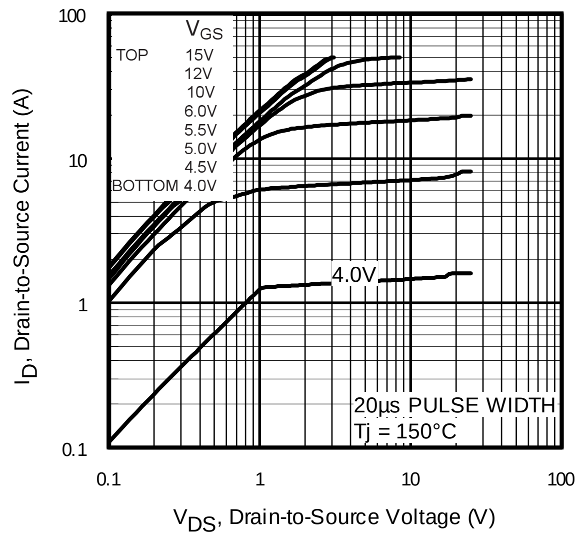


Fig 2. Typical Output Characteristics

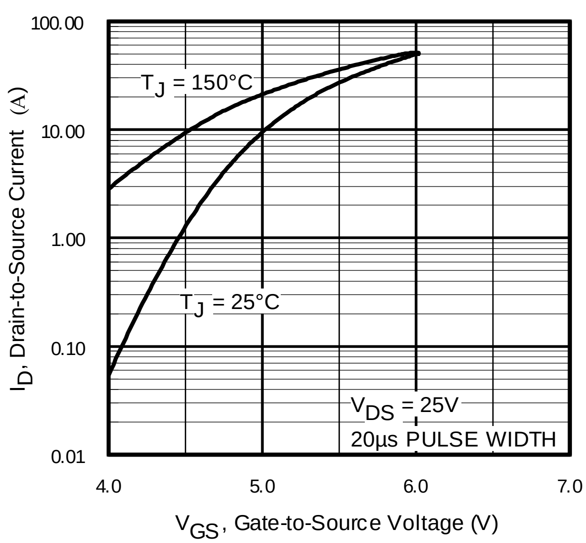


Fig 3. Typical Transfer Characteristics

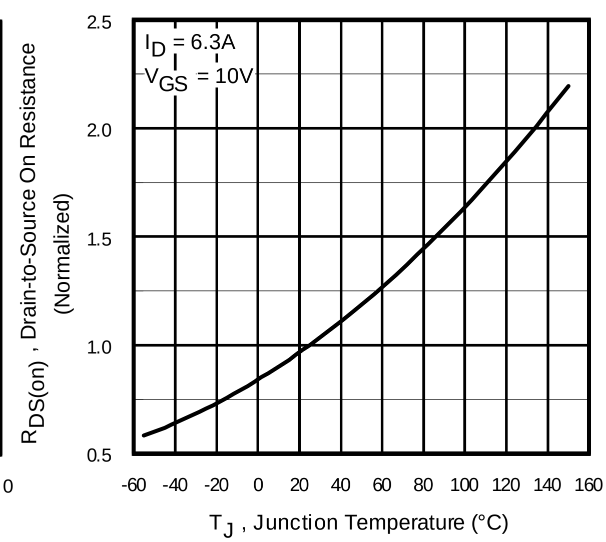


Fig 4. Normalized On-Resistance Vs. Temperature

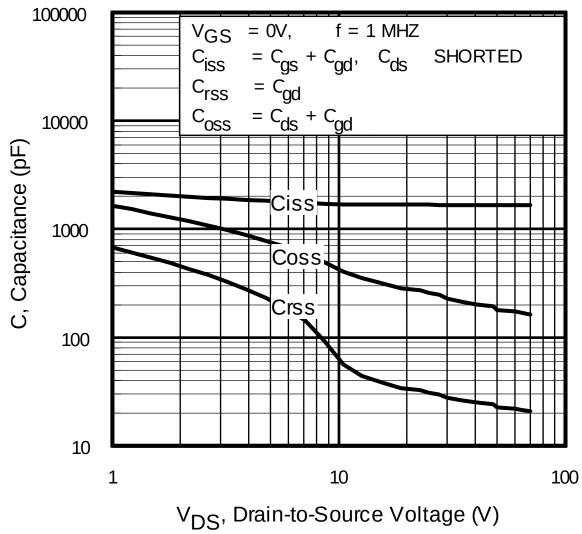


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

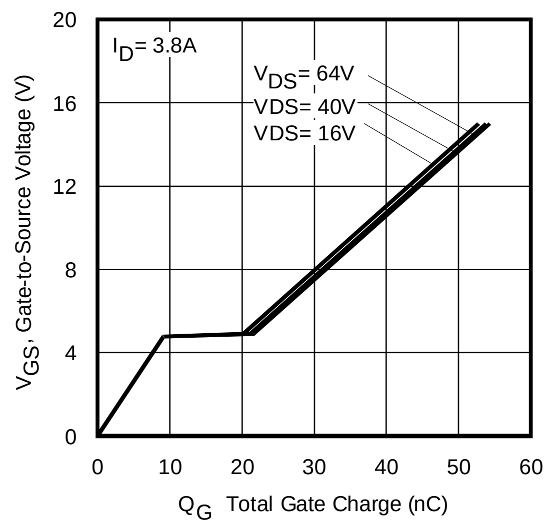


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

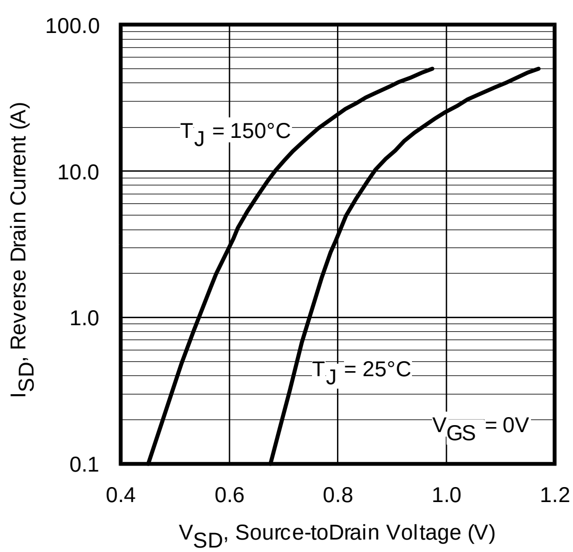


Fig 7. Typical Source-Drain Diode Forward Voltage

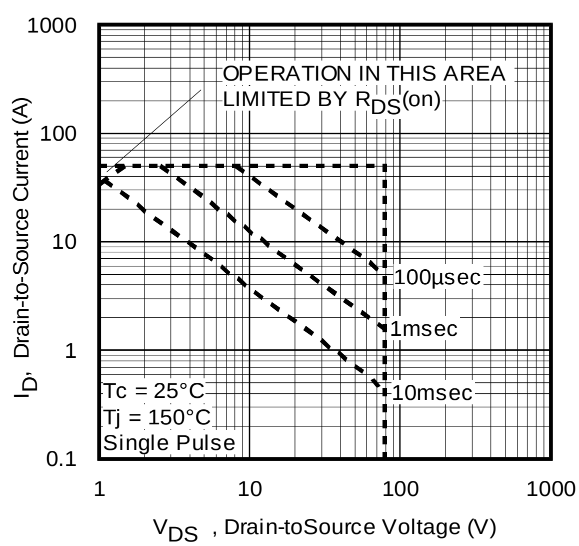


Fig 8. Maximum Safe Operating Area

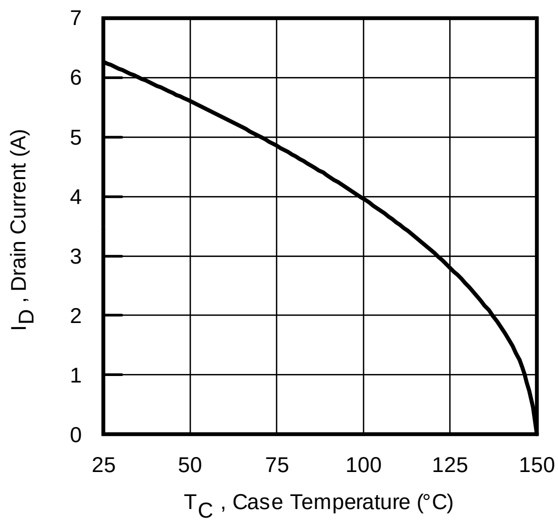


Fig 9. Maximum Drain Current Vs. Ambient Temperature

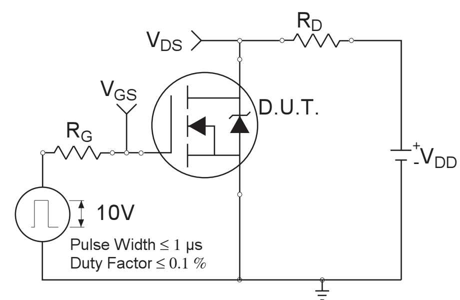


Fig 10a. Switching Time Test Circuit

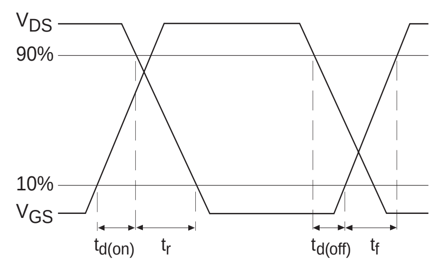


Fig 10b. Switching Time Waveforms

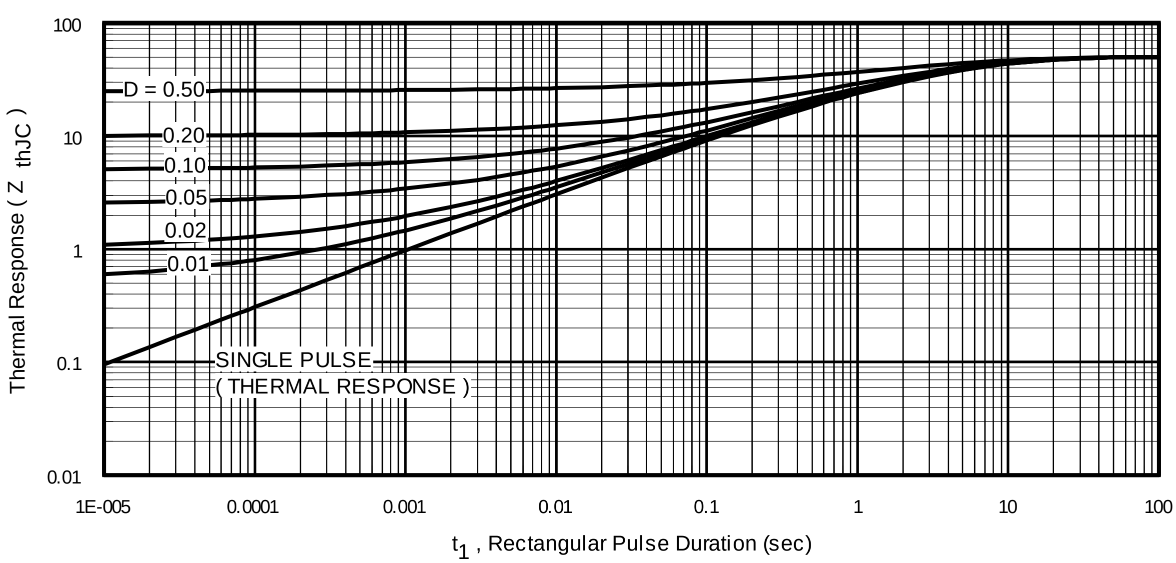


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

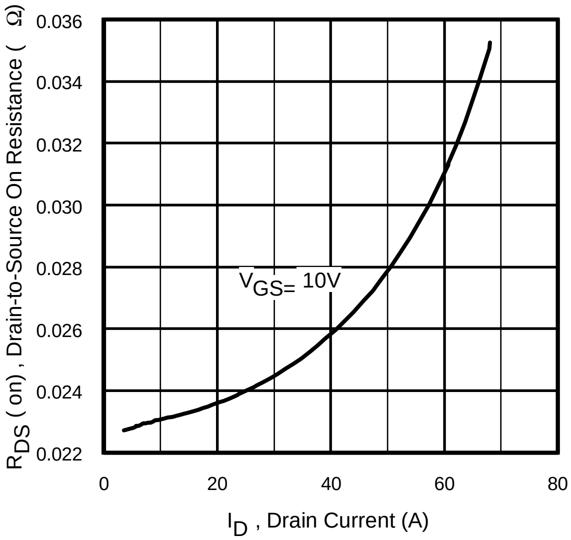


Fig 12. On-Resistance Vs. Drain Current

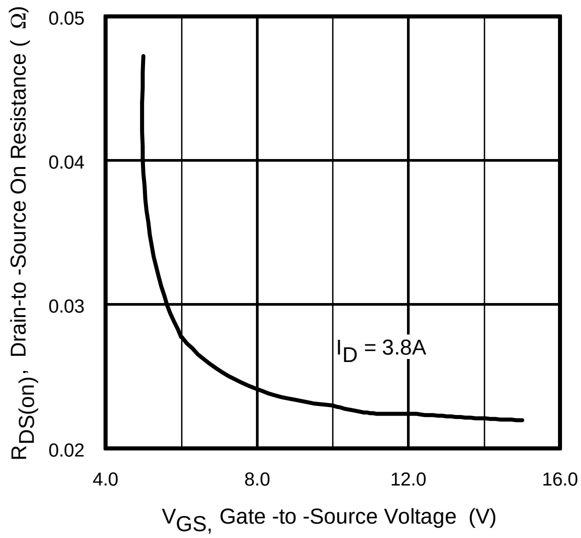


Fig 13. On-Resistance Vs. Gate Voltage

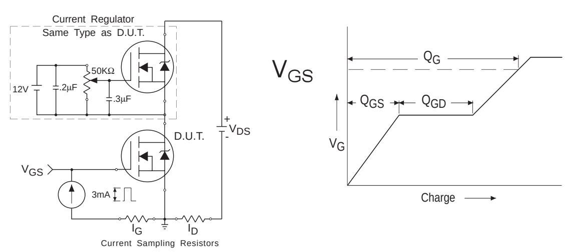
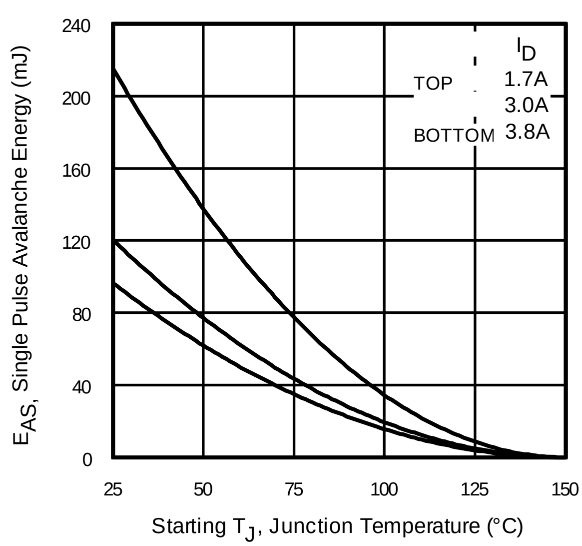


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform



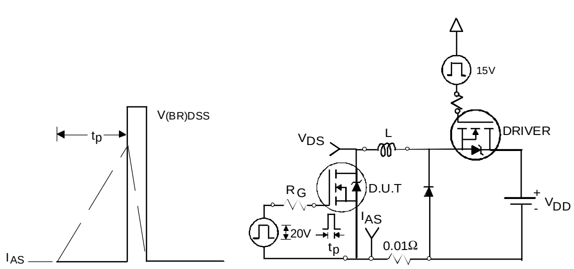


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

Fig 15c. Maximum Avalanche Energy Vs. Drain Current

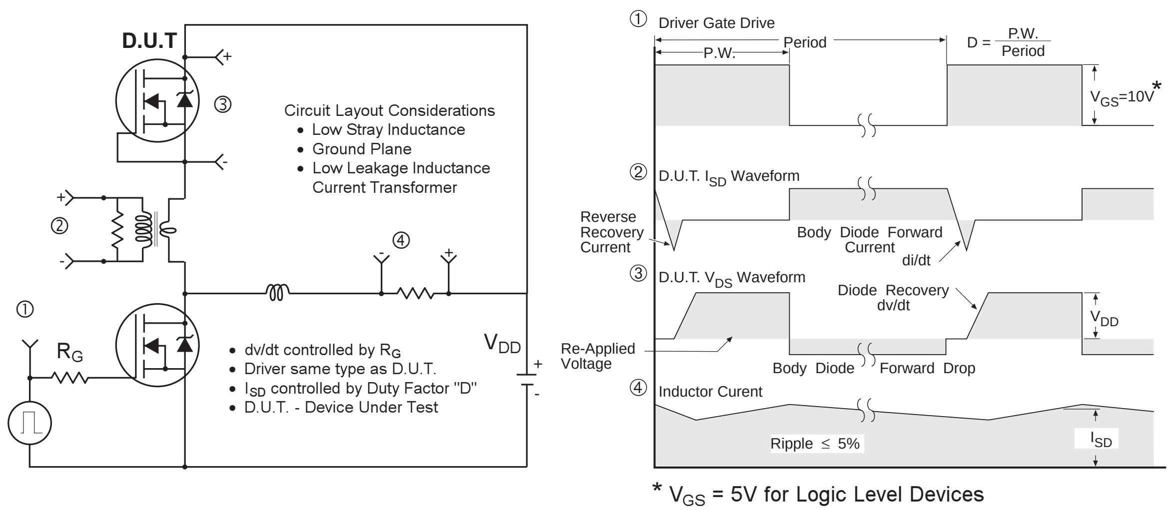


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

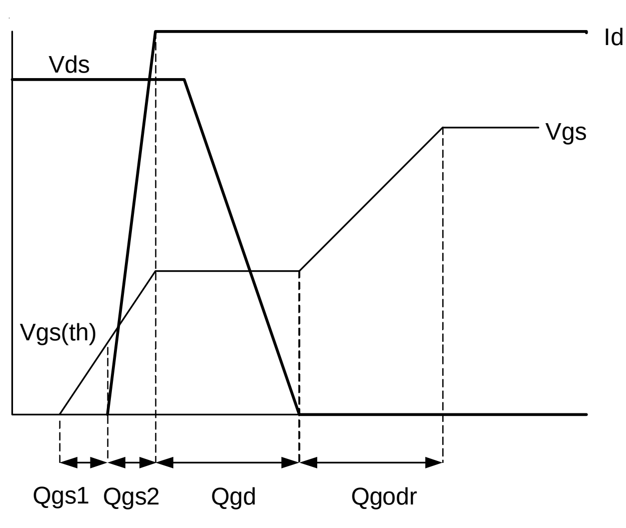
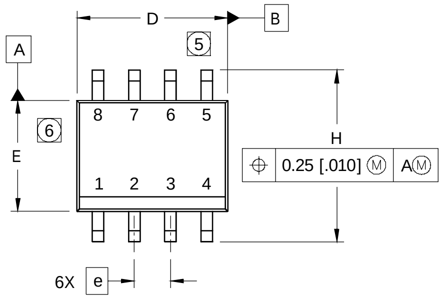


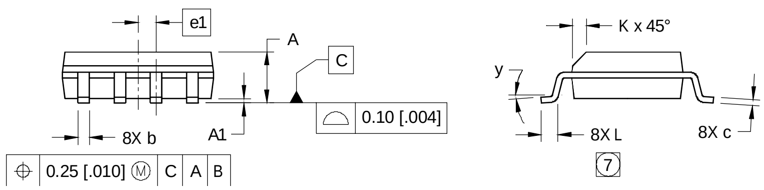
Fig 17. Gate Charge Waveform

SO-8 Package Outline

Dimensions are shown in millimeters (inches)



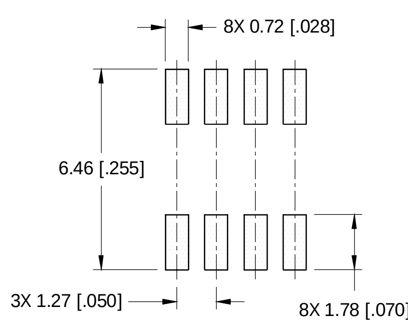
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

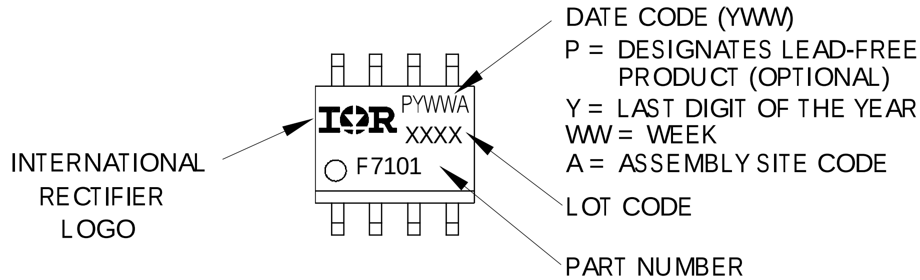
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT

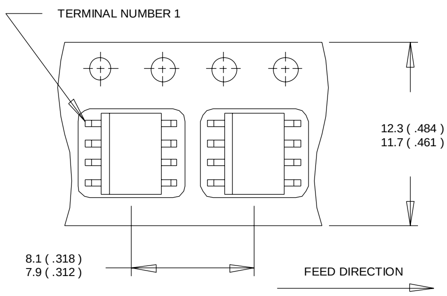


SO-8 Part Marking

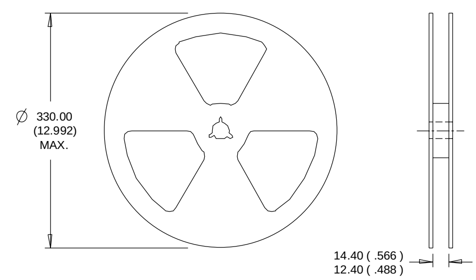
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



SO-8 Tape and Reel



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 13mH R_G = 25Ω, I_{AS} = 3.8A.

③ Pulse width ≤ 300µs; duty cycle ≤ 2%.

④ When mounted on 1 inch square copper board

⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.09/04

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics (“Beschaffenheitsgarantie”) .

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer’s compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer’s products and any use of the product of Infineon Technologies in customer’s applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer’s technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (**www.infineon.com**).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies’ products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.